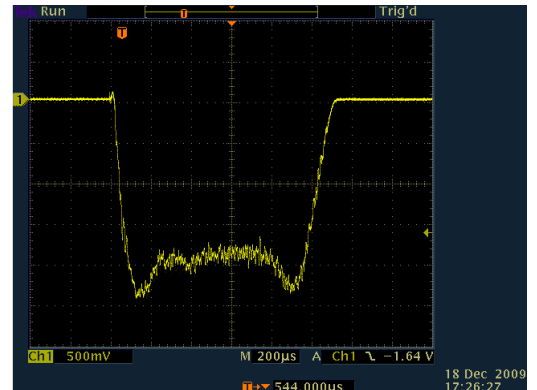
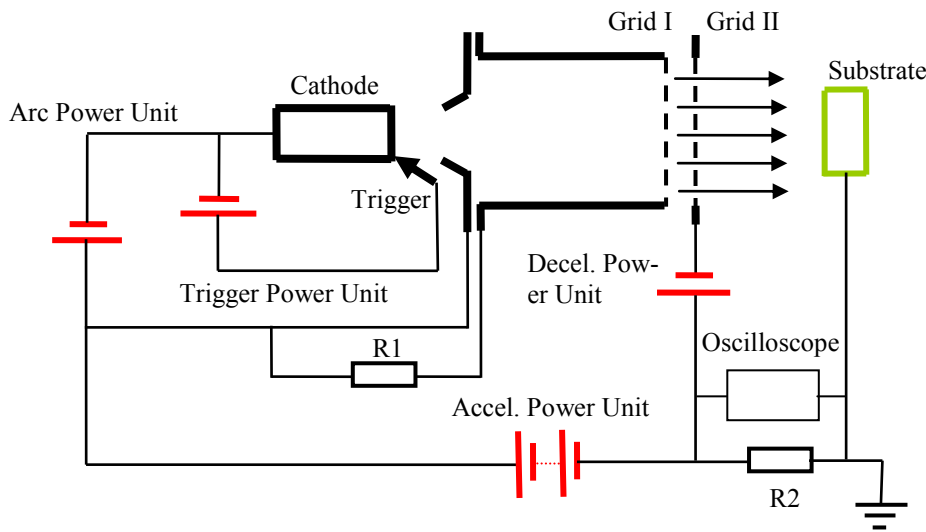


## Broad-Beam High Energy Ion Implanter

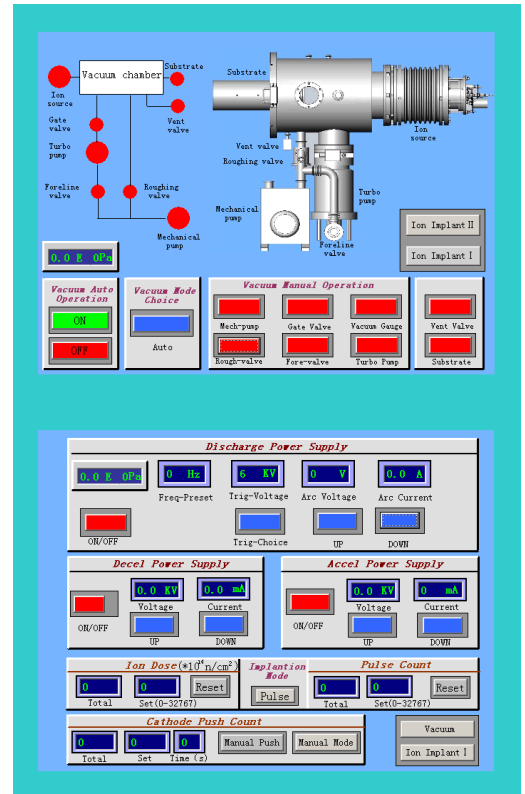


Model	HEMII- 80
Chamber	SS 304 steel, Φ400 mm x 500mm
Pumping System & Pumping Speed	Turbo-molecular pump and direct-joint rotary pump, pneumatic gate valve, foreline valve, roughing valve and vent valve
Ultimate Pressure	Better than $8 \times 10^{-5}$ Pa
Substrate	Φ150mm, Water cooling and satellite rotation
Metal Source	Pulse mode operation; Pulse width of 1ms; Pulse frequency of 30Hz
Output Voltage	30 kV — 80kV
Beam Size	>150mm
Non-uniformity	$\leq \pm 5\%$
Control	Touch-screen PLC control
Interlock & Protection	Vacuum & cooling water interlock, over-current & over-voltage protection



## Features

- **Ultra Broad Ion Beam for Large and High Uniform Implantation**
- **Widely Adjustable Ion Implantation Voltage**
- **Pure Metal and Alloyed Elements Implantation**
- **Real-time Implantation Dose Counting or Pulse Number Counting**
- **Substrate Independent**
- **Easy Touch-control**



## Main Applications

- To dope semiconducting, nano/micro-structural materials with foreign elements
- To produce high energy metal ions for surface modification
- To change the surface composition of materials
- To do the surface irradiation so as to form different microstructures of materials